



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

2SA1416/2SC3646 — PNP / NPN Epitaxial Planar Silicon Transistor

High-Voltage Switching Applications

Features

- Adoption of FBET, MBIT processes
- High breakdown voltage and large current capacity
- Fast switching speed
- Ultrasmall size making it easy to provide high-density, small-sized hybrid IC's

Specifications () : 2SA1416

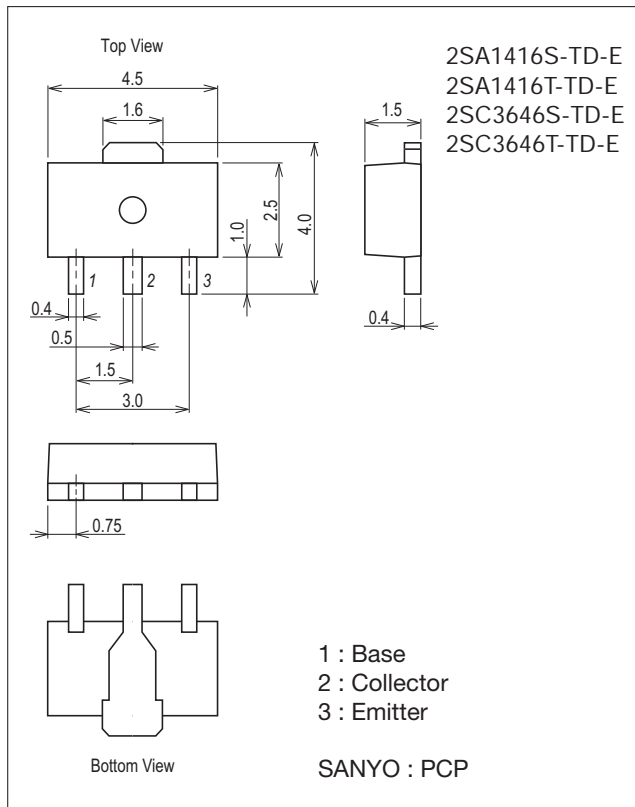
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(-)120	V
Collector-to-Emitter Voltage	VCEO		(-)100	V
Emitter-to-Base Voltage	VEBO		(-)6	V
Collector Current	IC		(-)1	A
Collector Current (Pulse)	ICP		(-)2	A
Collector Dissipation	PC		500	mW
		When mounted on ceramic substrate (250mm ² ×0.8mm)	1.3	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ)

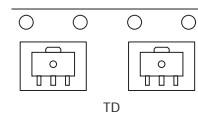
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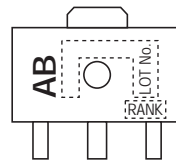
Product & Package Information

- Package : PCP
- JEITA, JEDEC : SC-62, SOT-89, TO-243
- Minimum Packing Quantity : 1,000 pcs./reel

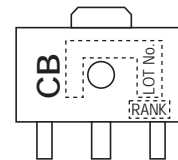
Packing Type: TD



Marking

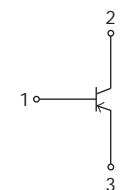


2SA1416

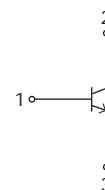


2SC3646

Electrical Connection



2SA1416



2SC3646

2SA1416 / 2SC3646

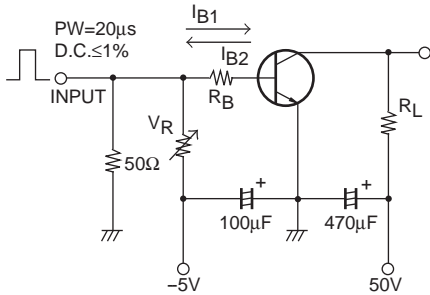
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)100V, I_E=0A$			(-)100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4V, I_C=0A$			(-)100	nA
DC Current Gain	h_{FE}	$V_{CE}=(-)5V, I_C=(-)100mA$	100*		400*	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10V, I_C=(-)100mA$		120		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10V, f=1MHz$		(13)8.5		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)400mA, I_B=(-)40mA$		(-0.2)0.1	(-0.6)0.4	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)400mA, I_B=(-)40mA$		(-)0.85	(-)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0A$	(-)120			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-)100			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0A$	(-)6			V
Turn-ON Time	t_{on}	See specified Test Circuit.		(80)80		ns
Storage Time	t_{stg}			(700)850		ns
Fall Time	t_f			(40)50		ns

* : The 2SA1416 / 2SC3646 are classified by 100mA h_{FE} as follows :

Rank	R	S	T
h_{FE}	100 to 200	140 to 280	200 to 400

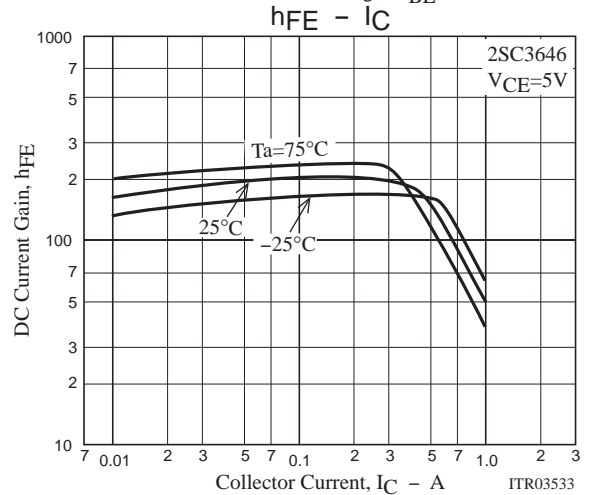
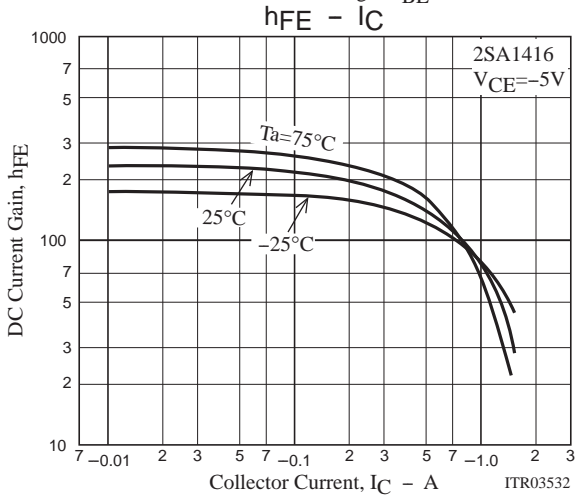
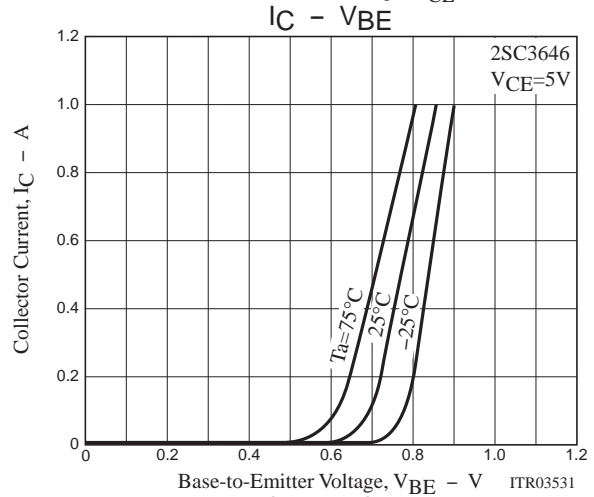
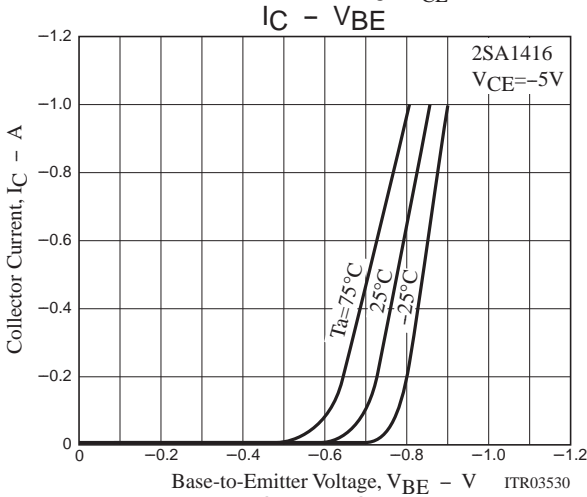
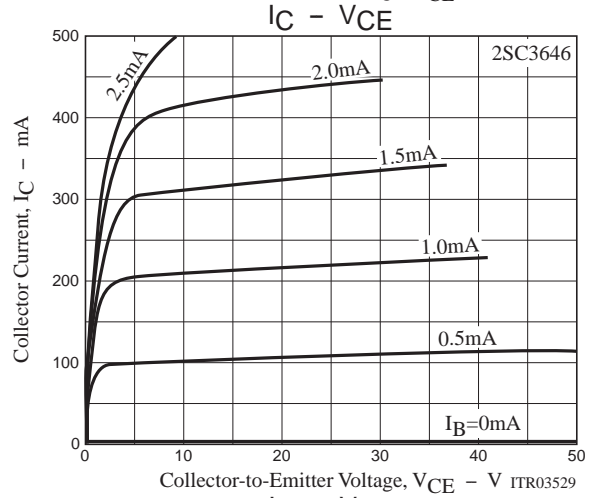
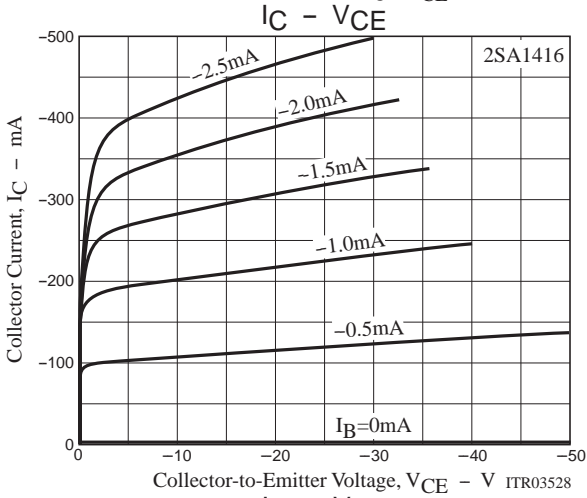
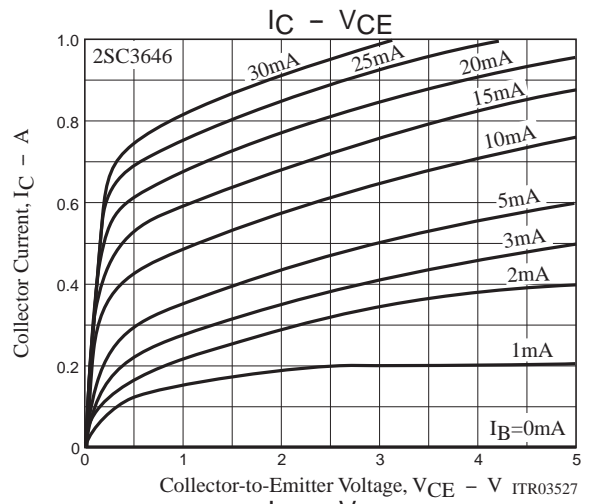
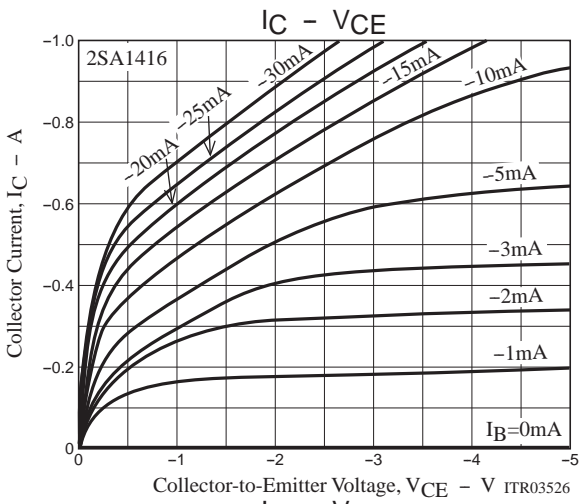
Switching Time Test Circuit

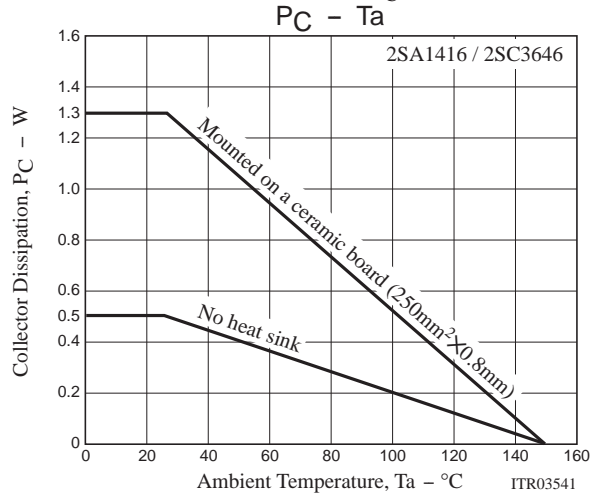
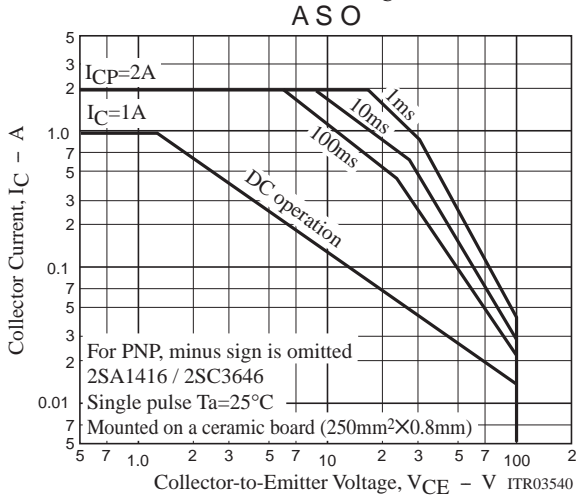
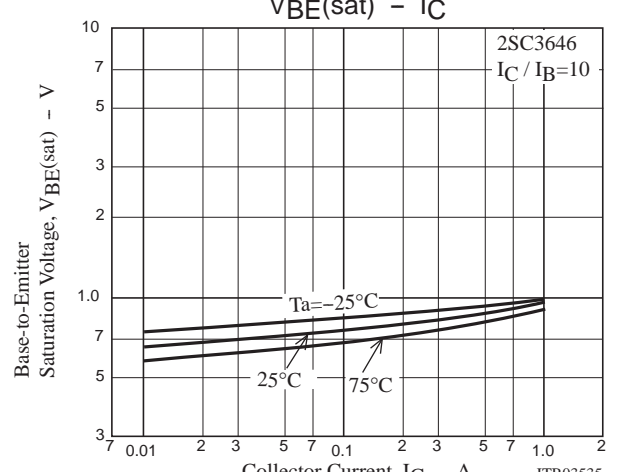
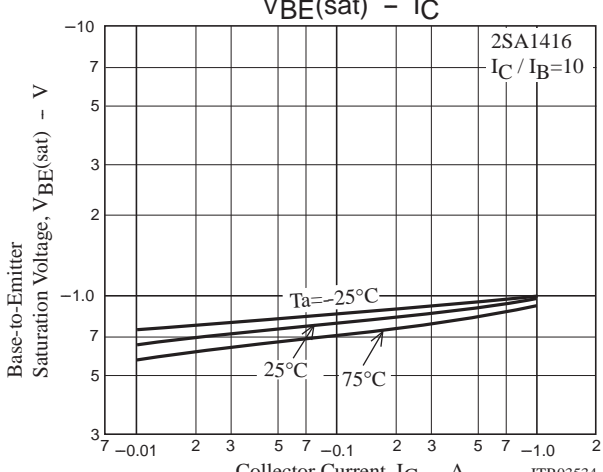
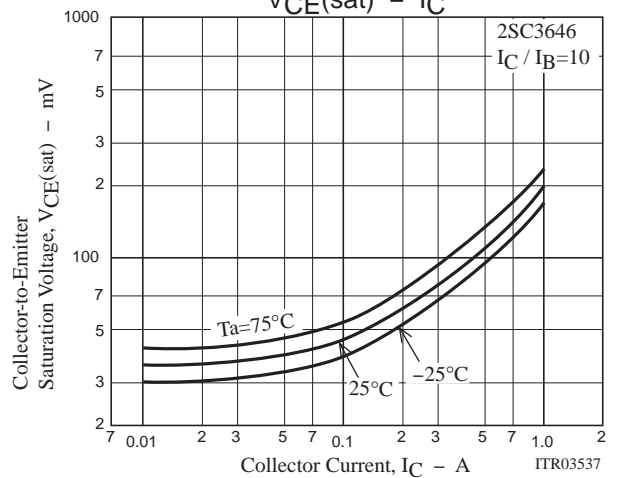
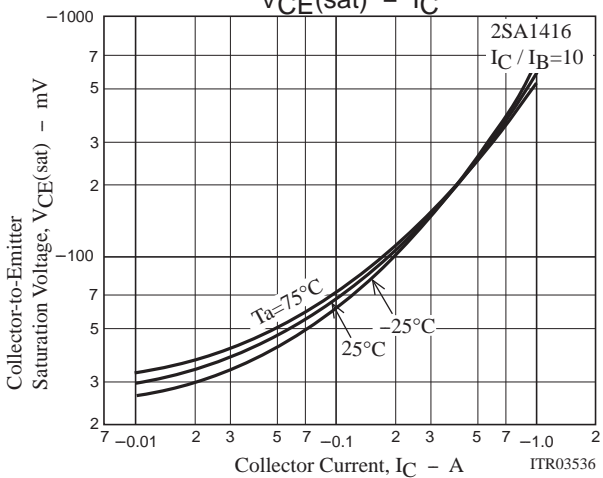
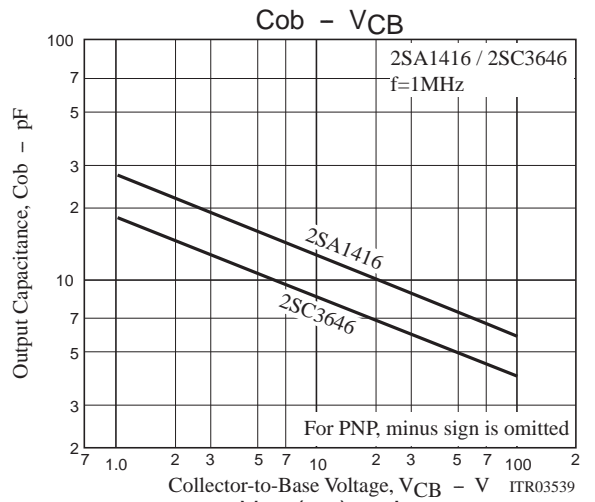
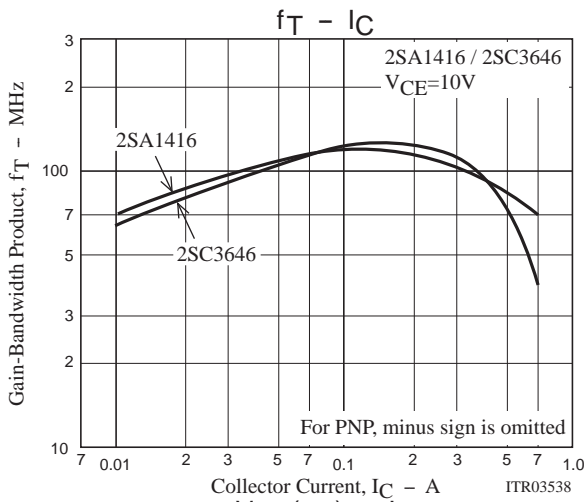


$I_C=10I_{B1}=-10I_{B2}=400mA$
 (For PNP, the polarity is reversed)

Ordering Information

Device	Package	Shipping	memo
2SA1416S-TD-E	PCP	1,000pcs./reel	Pb Free
2SA1416T-TD-E	PCP	1,000pcs./reel	
2SC3646S-TD-E	PCP	1,000pcs./reel	
2SC3646T-TD-E	PCP	1,000pcs./reel	





Bag Packing Specification

2SA1416S-TD-E, 2SA1416T-TD-E, 2SC3646S-TD-E, 2SC3646T-TD-E

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
PCP	PCP	1,000	4,000	24,000	4 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Reel label, Inner box label
(unit :mm)

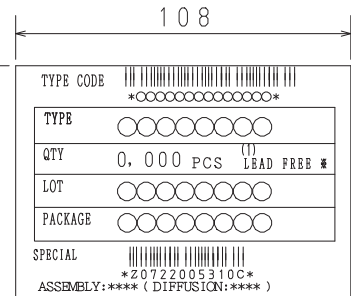
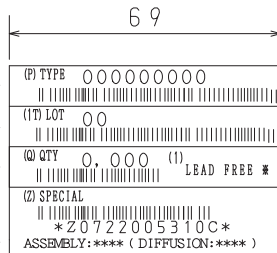
Outer box label
It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.

Packing method



Type No.
LOT No.
Quantity
Origin

Reel label



NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction



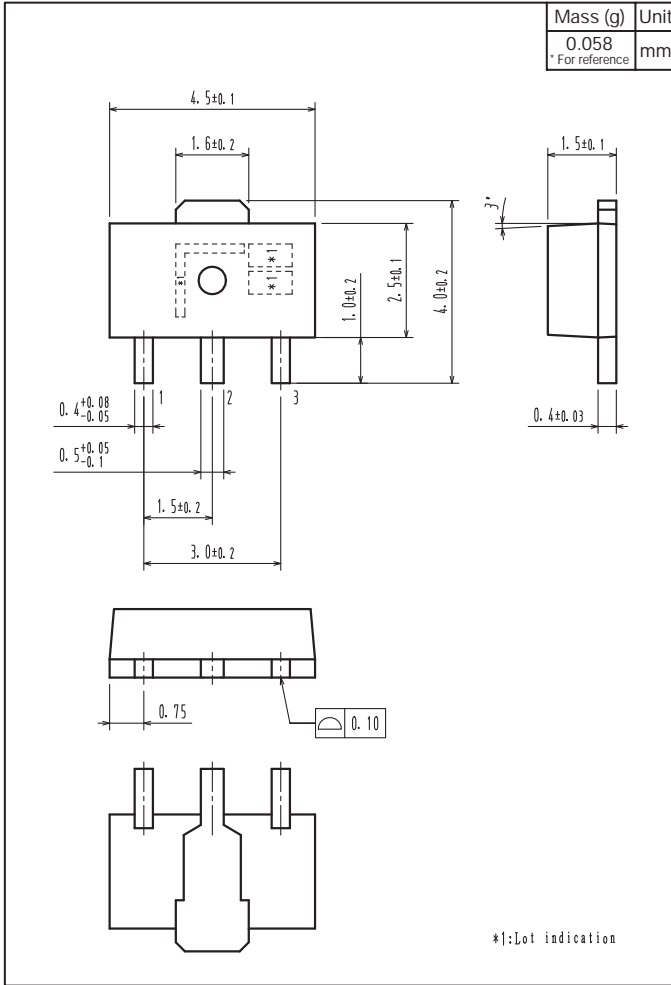
Those with pin 1 index on the feed hole side.....TD

2SA1416 / 2SC3646

Outline Drawing

Land Pattern Example

2SA1416S-TD-E, 2SA1416T-TD-E, 2SC3646S-TD-E, 2SC3646T-TD-E



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